

ABSTRACT

The invention concerns a lift-off process for patterning layers that are deposited and/or sputtered. The invention provides a two-layer resist and a patterning method using the
5 resist. The patterning method can readily produce burr-free layers on a substrate.

The method comprises the steps of:

sequentially applying positive radiation-sensitive resin compositions 1 and 2 to form a two-layer laminate;

10 subjecting the two-layer resist to single exposure and development to produce fine patterns having an undercut cross section;

depositing and/or sputtering an organic or inorganic thin layer with use of the resist pattern as a mask; and

15 lifting off the resist pattern to leave a pattern of the thin layer in desired shape.



162162



G00002